

Electronic Supplementary Information

Enhancement of crystalline quality and solar-blind photodetection characteristic of $\varepsilon\text{-Ga}_2\text{O}_3$ Film by introducing Zn impurity

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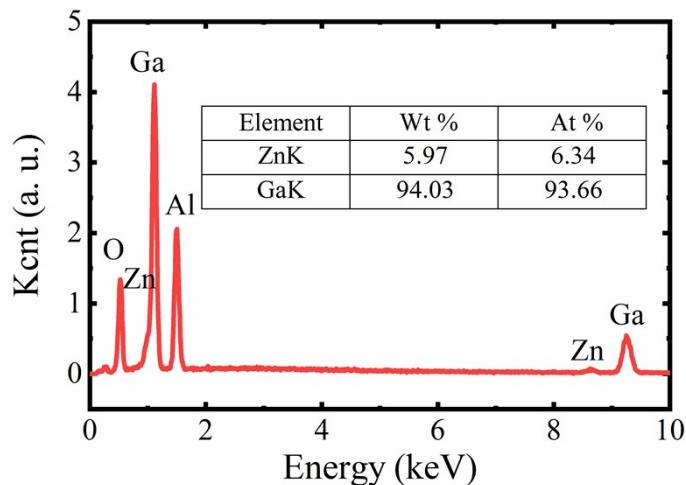


Figure S1 EDS spectrum of $\varepsilon\text{-Ga}_2\text{O}_3\text{:Zn}$.

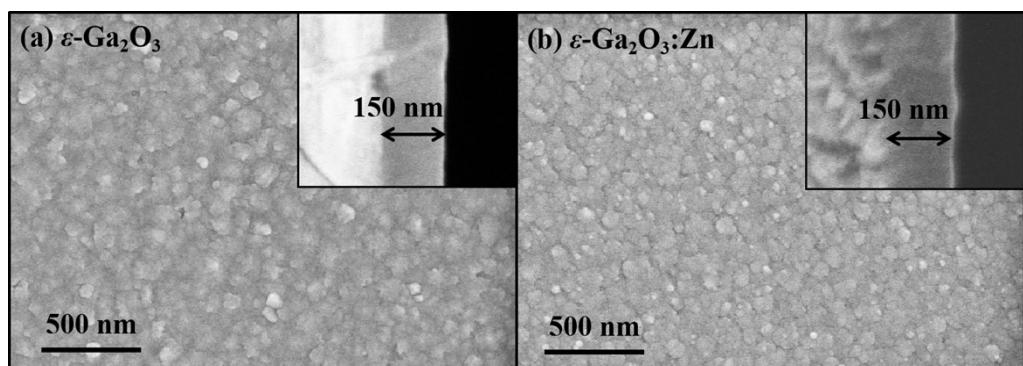


Figure S2 SEM images of (a) pure $\varepsilon\text{-Ga}_2\text{O}_3$ and (b) $\varepsilon\text{-Ga}_2\text{O}_3\text{:Zn}$.

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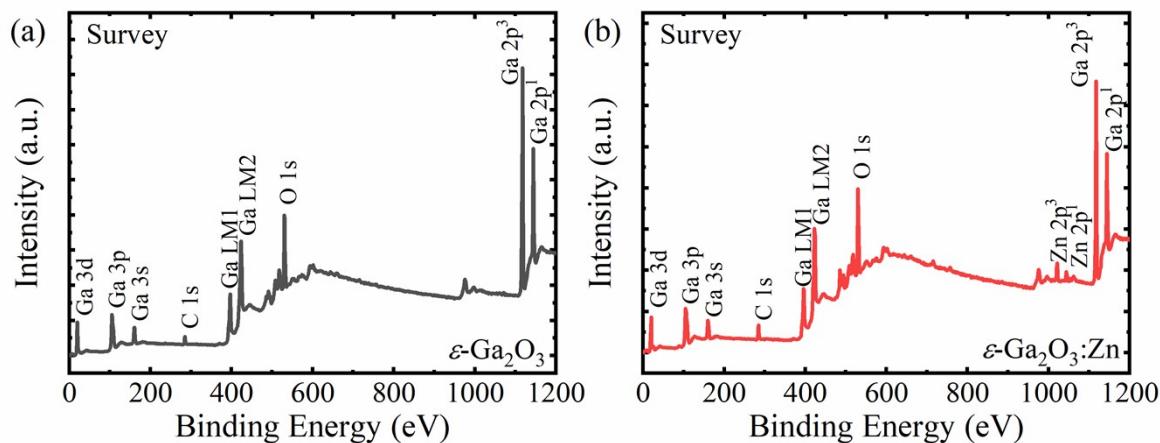


Figure S3 XPS survey spectra of (a) pure ε -Ga₂O₃ and (b) ε -Ga₂O₃:Zn.

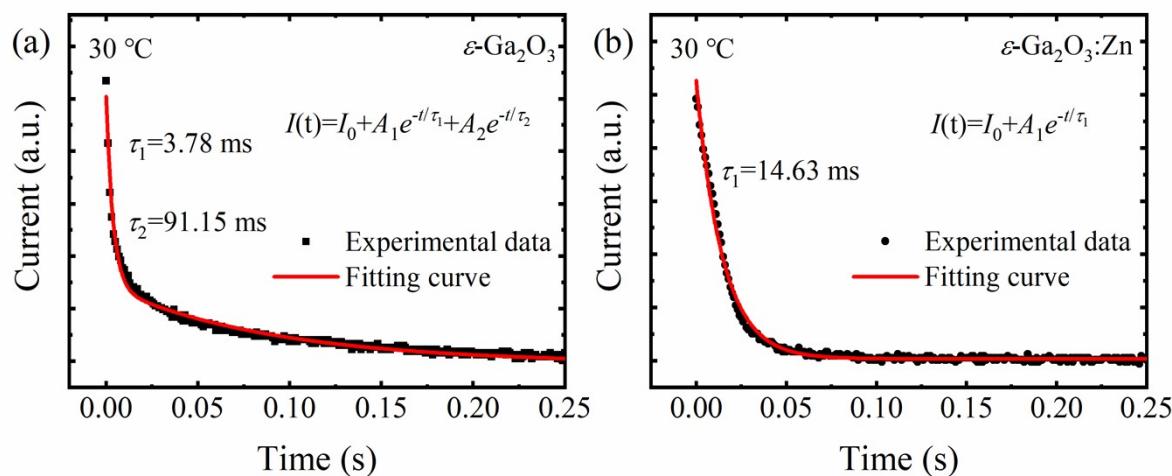


Figure S4 Typical decay curves of (a) ε -Ga₂O₃ and (b) Zn-doped ε -Ga₂O₃ detectors at 30 °C.